

## ABSTRACT

Disclosed is a light-emitting device (100) has a light-emitting layer portion (24) which is composed of a group III-V compound semiconductor and a transparent thick-film semiconductor layer (90) with a thickness of not less than  $40\text{ }\mu\text{m}$  which is formed on at least one major surface side of the light-emitting layer portion (24) and composed of a group III-V compound semiconductor having a band gap energy larger than the photon energy equivalent of the peak wavelength of emission flux from the light-emitting layer portion (24). The transparent thick-film semiconductor layer (90) has a lateral surface portion (90S) which is a chemically etched surface. The dopant concentration of the transparent thick-film semiconductor layer (90) is not less than  $5 \times 10^{16}/\text{cm}^3$  and not more than  $2 \times 10^{18}/\text{cm}^3$ . The light-emitting device can have a transparent thick-film semiconductor layer while being significantly improved in light taking-out efficiency from the lateral surface portion.